

Pradip Dalapati

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1926917/publications.pdf>

Version: 2024-02-01

28
papers

230
citations

840776

11
h-index

1058476

14
g-index

28
all docs

28
docs citations

28
times ranked

132
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of temperature on the intensity and carrier lifetime of an AlGaAs based red light emitting diode. Journal of Semiconductors, 2013, 34, 092001.	3.7	19
2	Current-induced degradation process in (In)AlGaIn-based deep-UV light-emitting diode fabricated on AlN/sapphire template. Optical Materials, 2020, 109, 110352.	3.6	19
3	Influence of temperature on the performance of high power AlGaInP based red light emitting diode. Optical and Quantum Electronics, 2015, 47, 1227-1238.	3.3	18
4	A photonic atom probe coupling 3D atomic scale analysis with in situ photoluminescence spectroscopy. Review of Scientific Instruments, 2020, 91, 083704.	1.3	16
5	Study of effective carrier lifetime and ideality factor of BPW 21 and BPW 34B photodiodes from above room temperature to liquid nitrogen temperature. Cryogenics, 2015, 65, 10-15.	1.7	13
6	Investigation of AlGaIn/GaN high electron mobility transistors on Silicon (111) substrates employing multi-stacked strained layer superlattice structures. Superlattices and Microstructures, 2020, 147, 106709.	3.1	13
7	Influence of temperature on tunneling-enhanced recombination in Si based p-n photodiodes. Journal of Semiconductors, 2014, 35, 082001.	3.7	12
8	Tunneling current in Si-doped n type-GaAs heterostructures infrared emitter. Frontiers of Optoelectronics, 2014, 7, 501-508.	3.7	12
9	Impact of current-induced degradation process on the electro-optical characteristics of InGaIn/GaN multiple-quantum-well photodetectors fabricated on sapphire substrate. Applied Physics Letters, 2021, 118, .	3.3	12
10	Bias-controlled photocurrent generation process in GaN-based ultraviolet p-n photodetectors fabricated with a thick Al ₂ O ₃ passivation layer. Optik, 2021, 245, 167691.	2.9	12
11	Evaluation of high-performance, self-powered and wavelength-selective InGaIn/GaN multiple quantum well UV photodetectors fabricated on sapphire substrate: Analysis of the influence of growth temperature. Sensors and Actuators A: Physical, 2021, 331, 113050.	4.1	11
12	Studies on the Effect of Temperature on Electroluminescence, Current-Voltage, and Carrier Lifetimes Characteristics in a InGaIn/Sapphire Purple Light Emitting Diode. Journal of Electronic Materials, 2016, 45, 2683-2691.	2.2	8
13	Super-resolution Optical Spectroscopy of Nanoscale Emitters within a Photonic Atom Probe. Nano Letters, 2020, 20, 8733-8738.	9.1	8
14	Temperature dependence of current-voltage and carrier lifetime characteristics in InGaIn blue light-emitting diode. Optical and Quantum Electronics, 2020, 52, 1.	3.3	6
15	<i>In Situ</i> Spectroscopic Study of the Optomechanical Properties of Evaporating Field Ion Emitters. Physical Review Applied, 2021, 15, .	3.8	6
16	Effect of temperature on light-current (L-I) characteristics of GaAlAs based infrared emitter. Optik, 2015, 126, 2242-2246.	2.9	5
17	Effect of temperature on the opto-electrical properties of GaP based light emitting diodes. Optik, 2016, 127, 2598-2602.	2.9	5
18	Influence of temperature on different optoelectronic characteristics of InGaIn light emitting diodes. Optical and Quantum Electronics, 2017, 49, 1.	3.3	5

#	ARTICLE	IF	CITATIONS
19	InGaN Quantum Dots Studied by Correlative Microscopy Techniques for Enhanced Light-Emitting Diodes. ACS Applied Nano Materials, 2020, 3, 10133-10143.	5.0	5
20	Understanding the degradation mechanisms of InGaN/GaN multiple quantum well UV photodetectors submitted to different current stresses. Optics Letters, 2021, 46, 3568.	3.3	5
21	The role of p-GaN layer thickness for the evaluation of high-performance and ultrafast GaInN/GaN multiple quantum wells UV photodetectors. Optical Materials, 2022, 127, 112284.	3.6	5
22	Improved epilayer qualities and electrical characteristics for GaInN multiple-quantum-well photovoltaic cells and their operation under artificial sunlight and monochromatic light illuminations. AIP Advances, 2021, 11, .	1.3	4
23	Analysis of the Temperature Dependence of Diode Ideality Factor in InGaN-Based UV-A Light-Emitting Diode. Semiconductors, 2020, 54, 1284-1289.	0.5	3
24	Effect of Temperature on Electro-Optical Characteristics of Silicon Based p-n Photodiode (VTB8440BH). Silicon, 2018, 10, 2547-2553.	3.3	2
25	Reliability of Ultraviolet Light-Emitting Diodes. Solid State Lighting Technology and Application Series, 2019, , 397-424.	0.3	2
26	Temperature induced carrier transition and its effect on optical intensity of InGaN-based light-emitting diodes. Optik, 2020, 212, 164722.	2.9	2
27	Effect of temperature on intensity and forward tunneling current in GaP-based green light emitting diode. Journal of Optics (India), 2017, 46, 68-74.	1.7	1
28	Polarization-resolved photoluminescence study of an atom probe tip containing a ZnO-(Mg,Zn)O heterostructure. , 2022, , .		1